

Materials List for:

Plasma-assisted Molecular Beam Epitaxy of N-polar InAlN-barrier High-electron-mobility Transistors

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Materials

Name	Company	Catalog Number	Comments
Freestanding N-polar GaN wafer	Kyma		10 mm x 10 mm
C-polar SiC wafer	Cree	W4TRE0R-L600	3 inch diameter
Microelectronics grade acetone	Fischer Scientific	A18-4	
Microelectronics grade isopropanol	J.T. Baker	9079-05/JT9079-5	
Al source material (6N5 pure)	UMC	ALR62060I	
Ga source material (7N pure)	UMC	GA701	
In source material (7N pure)	UMC	IN750	
ULSI N ₂ source gas (6N pure)	Matheson Tri-gas	G2659906D	
PRO-75 MBE system	OmicronScientia		